

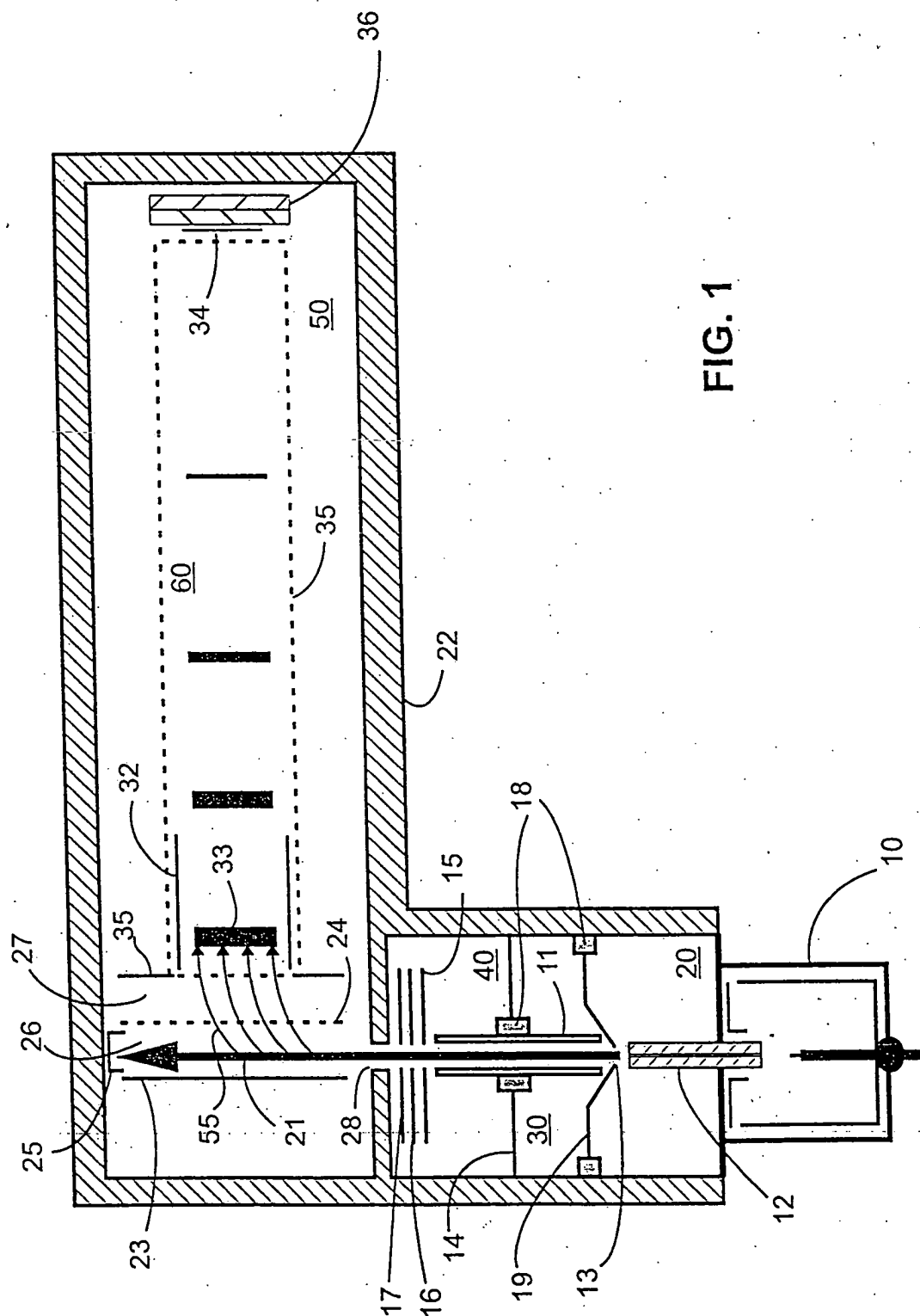
[illegible]

FIG. 1

#3

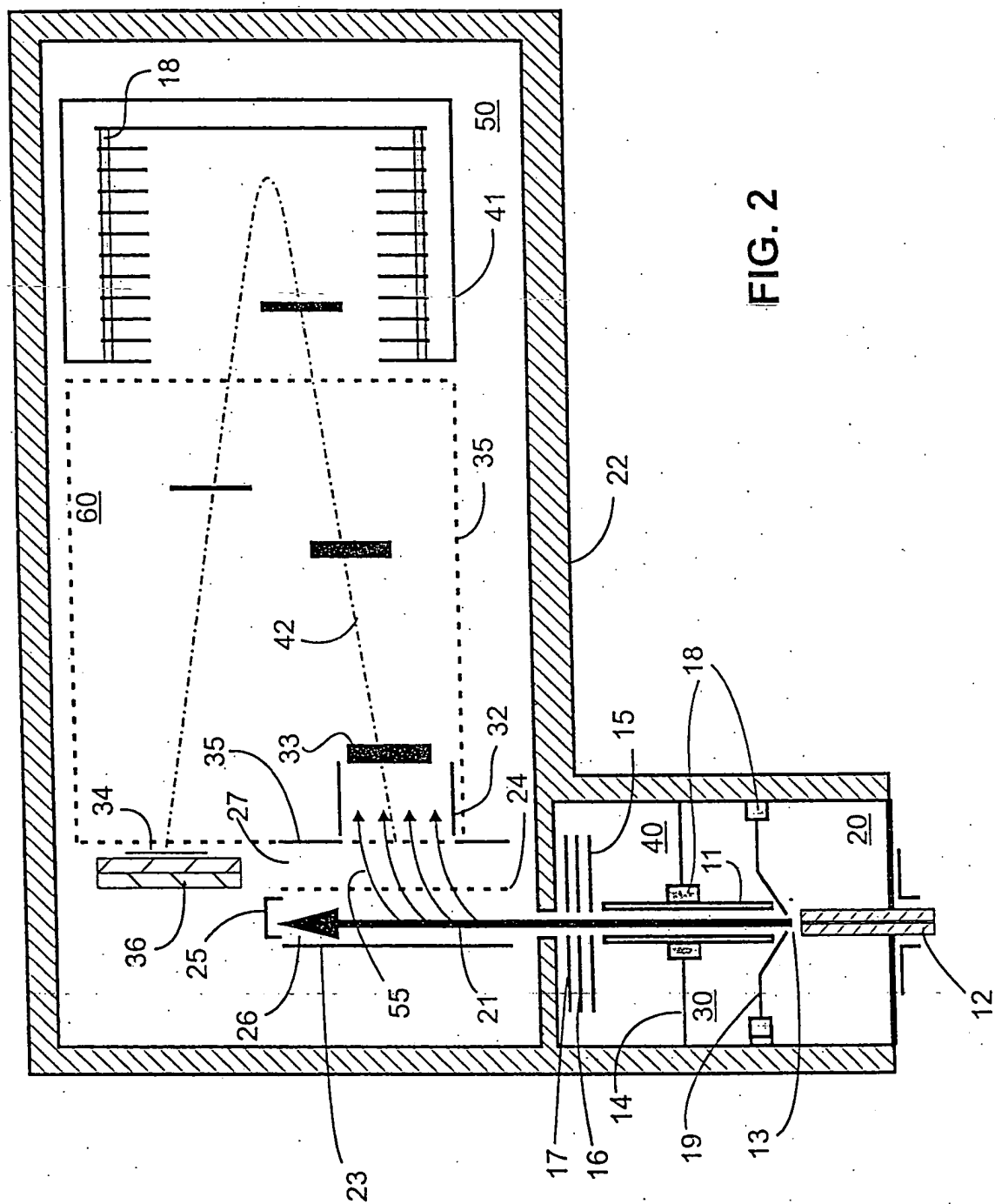


FIG. 2

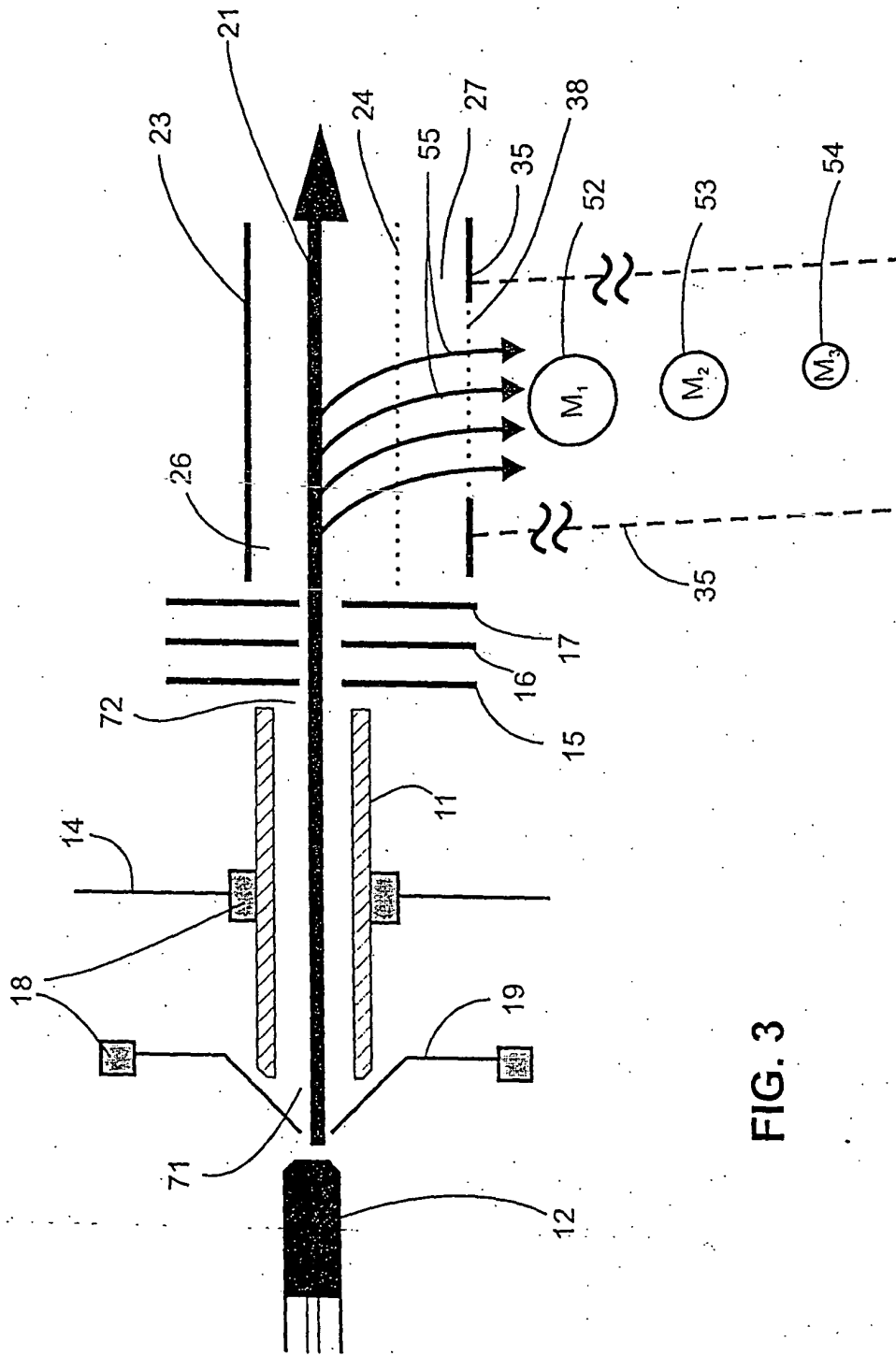


FIG. 3

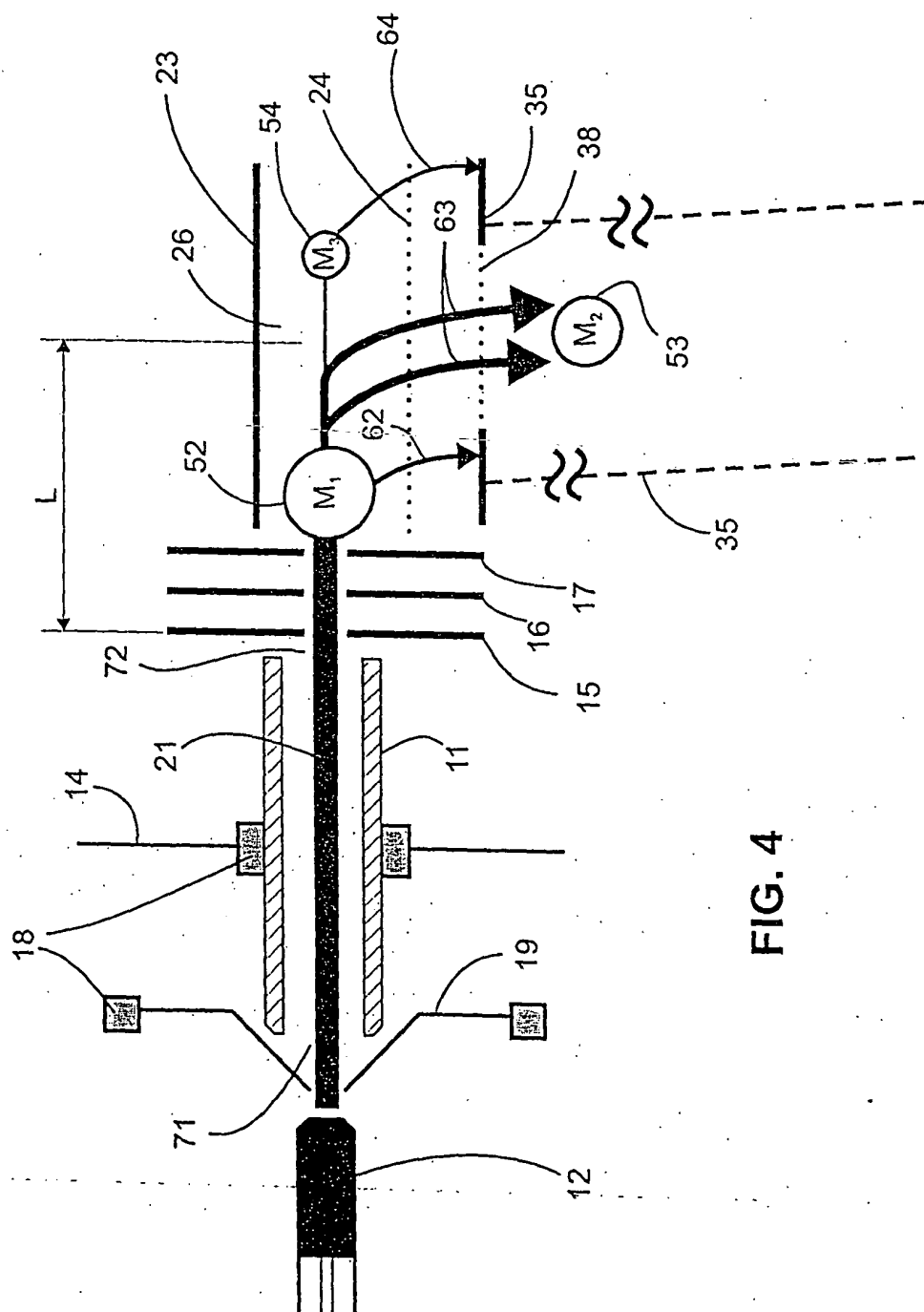


FIG. 4

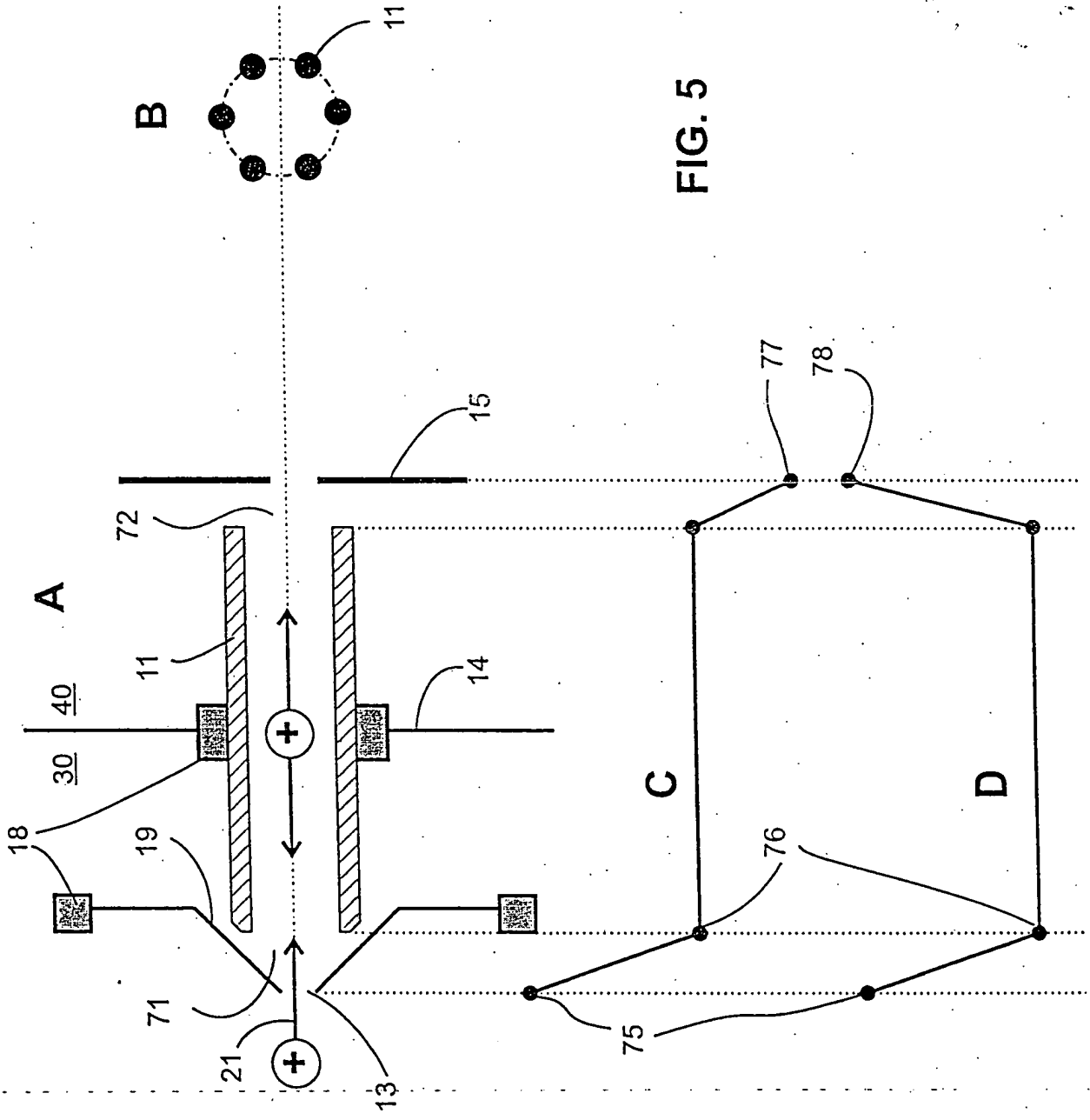


FIG. 5

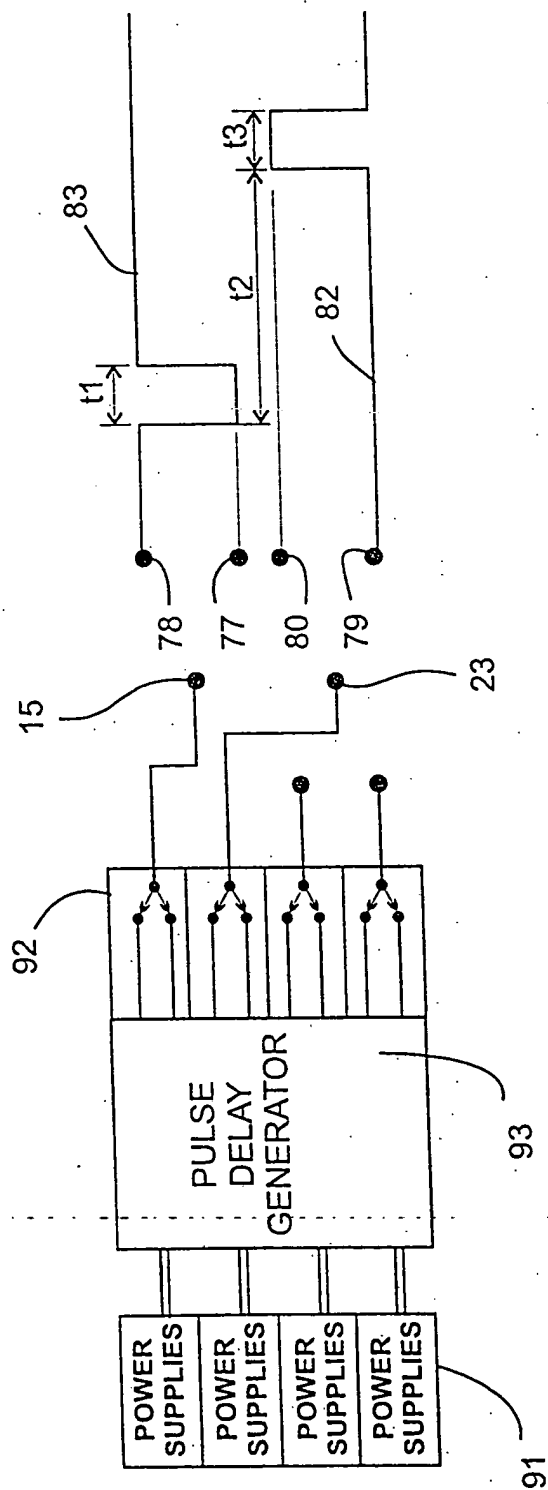


FIG. 6

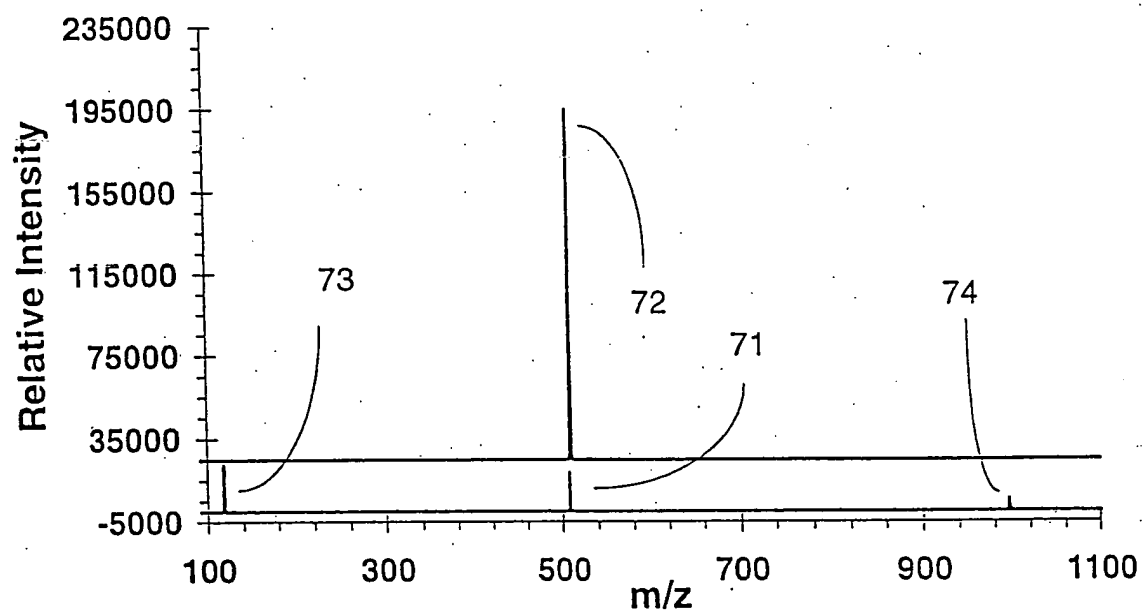


FIG. 7A

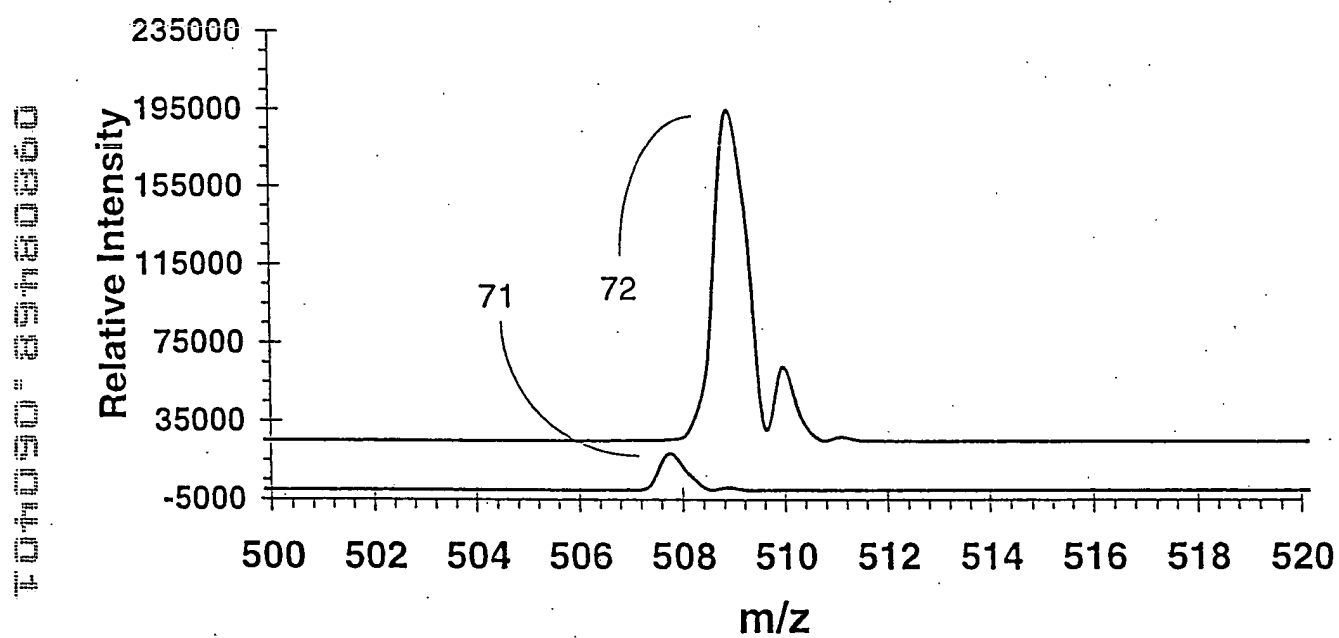


FIG. 7B

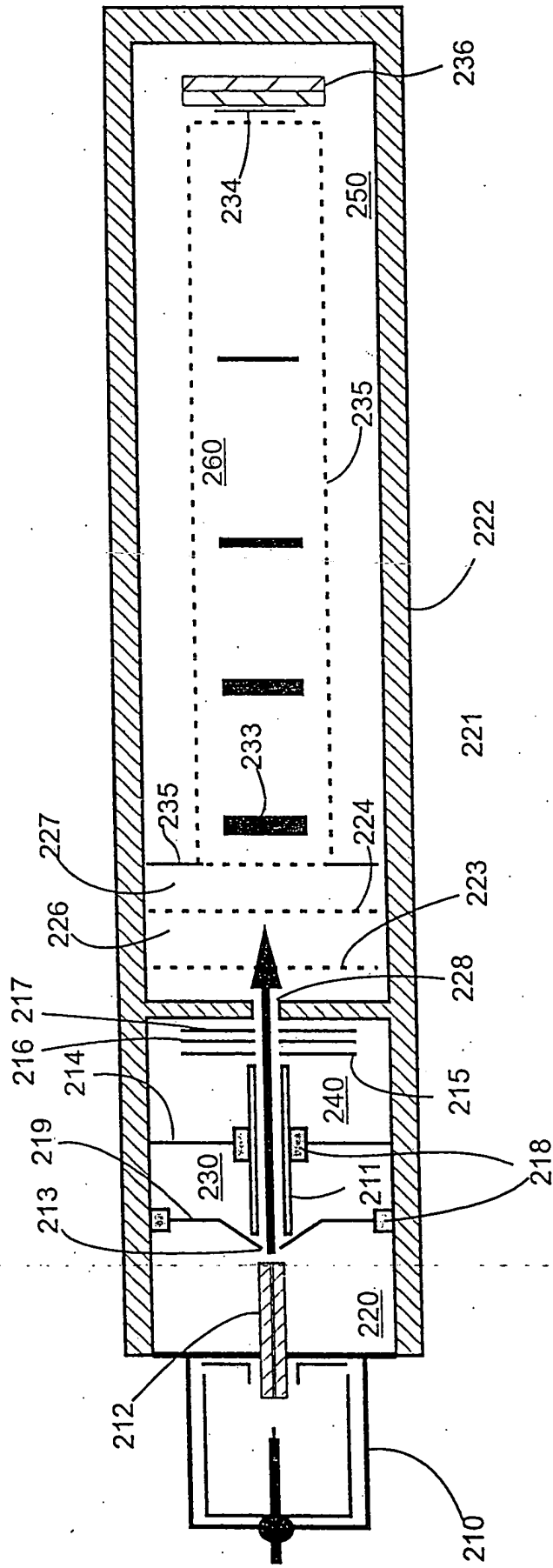
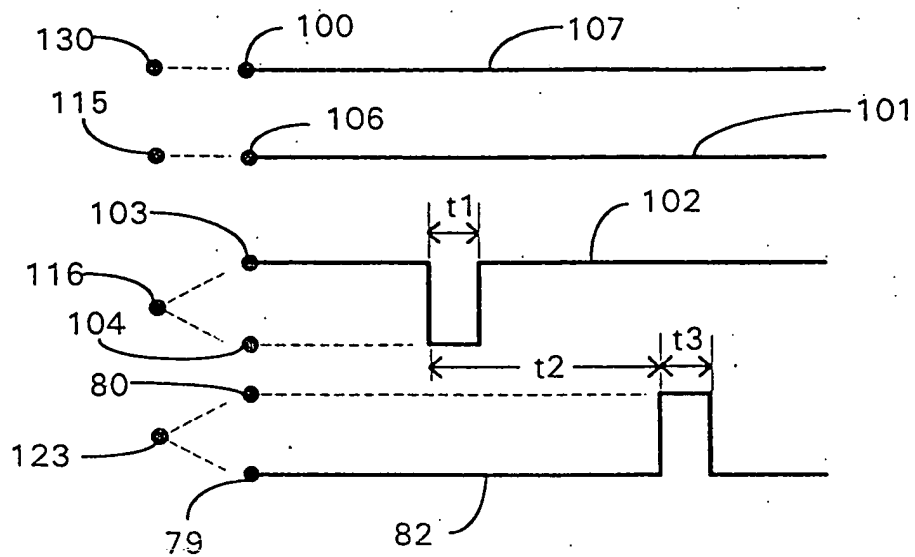
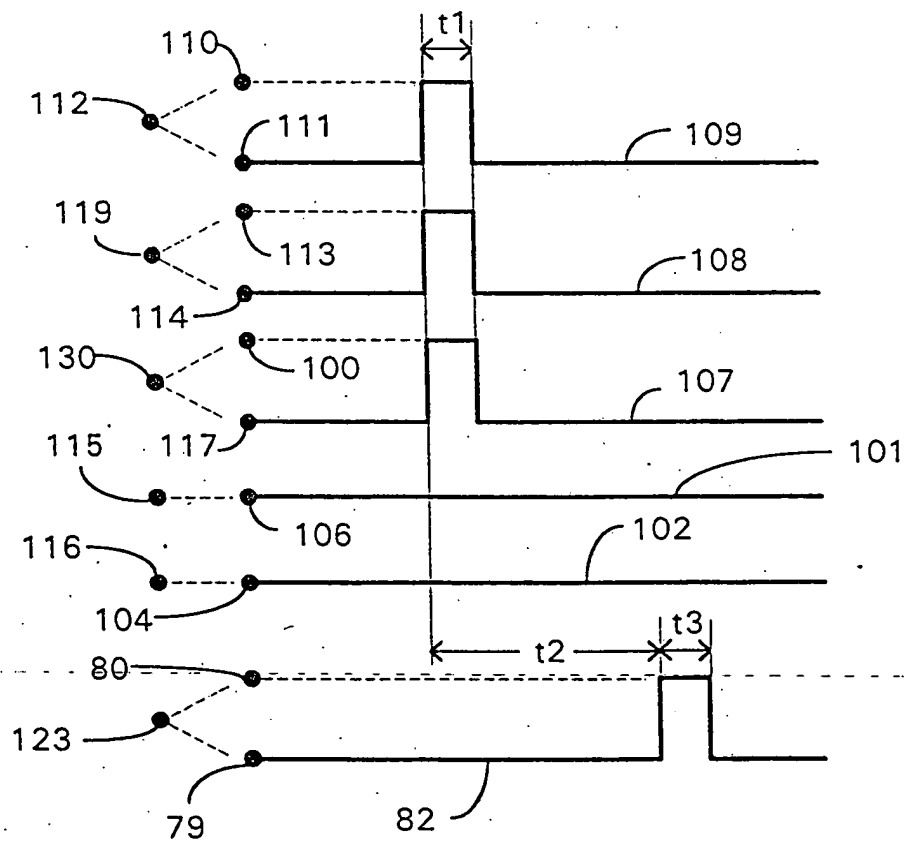


FIG. 8



A

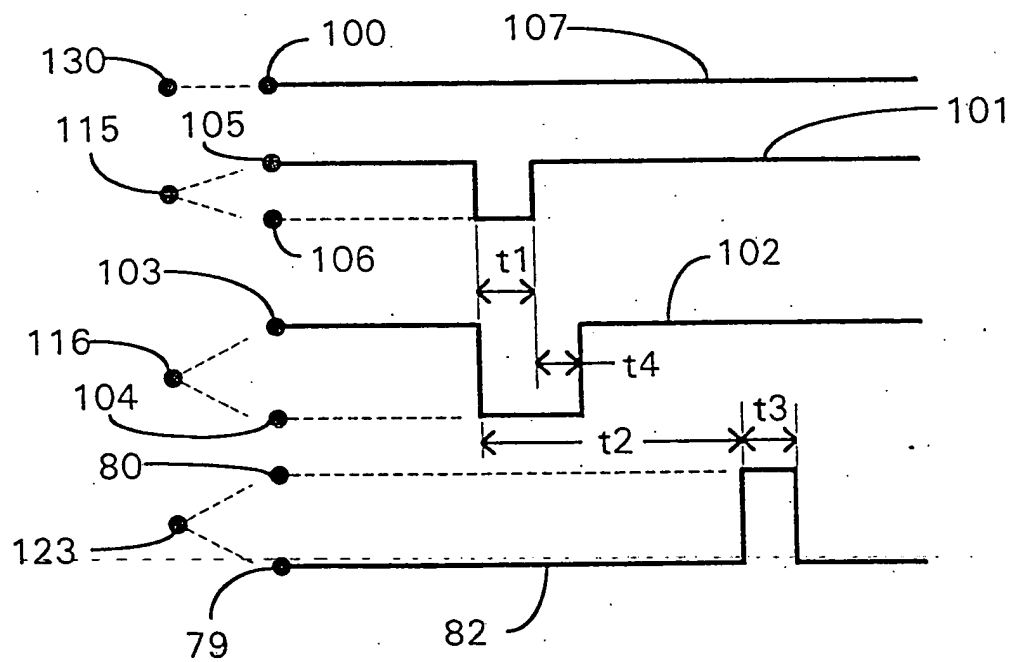


B

FIG. 9

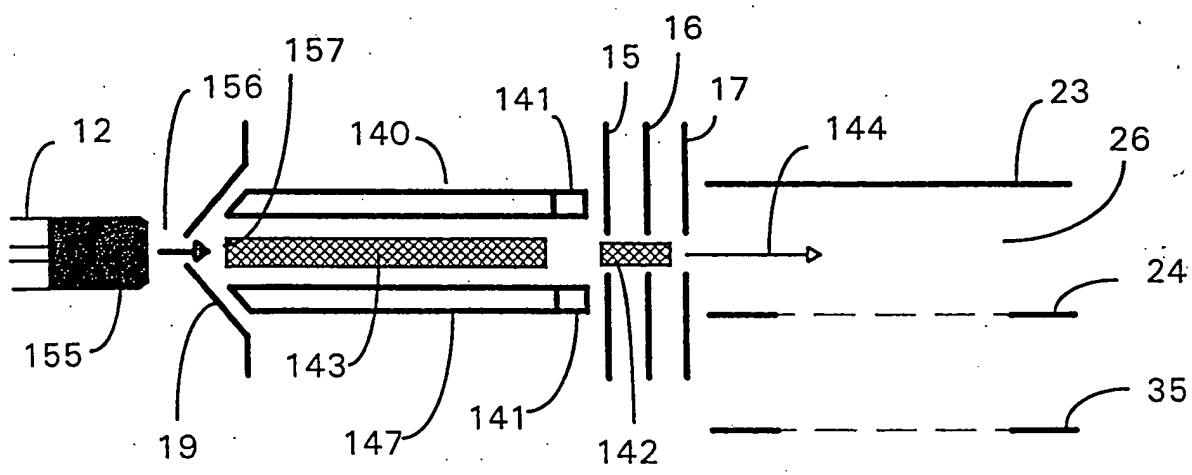
This diagram shows a cross-sectional view of a semiconductor device. It features a central trench structure. The top layer is labeled 107. Below it is a layer 101. A layer 102 is located on the right side of the trench. The trench itself is defined by a central region 100 and side regions 103 and 106. The bottom of the trench is labeled 80. The bottom layer is labeled 82. Various other labels include 130, 115, 105, 116, 104, 123, 79, and 107. Dimensions t1, t2, and t3 are indicated with arrows. Dashed lines connect points 130, 115, 105, 116, 104, and 123 to points 100, 103, 106, 80, and 79 respectively.

A

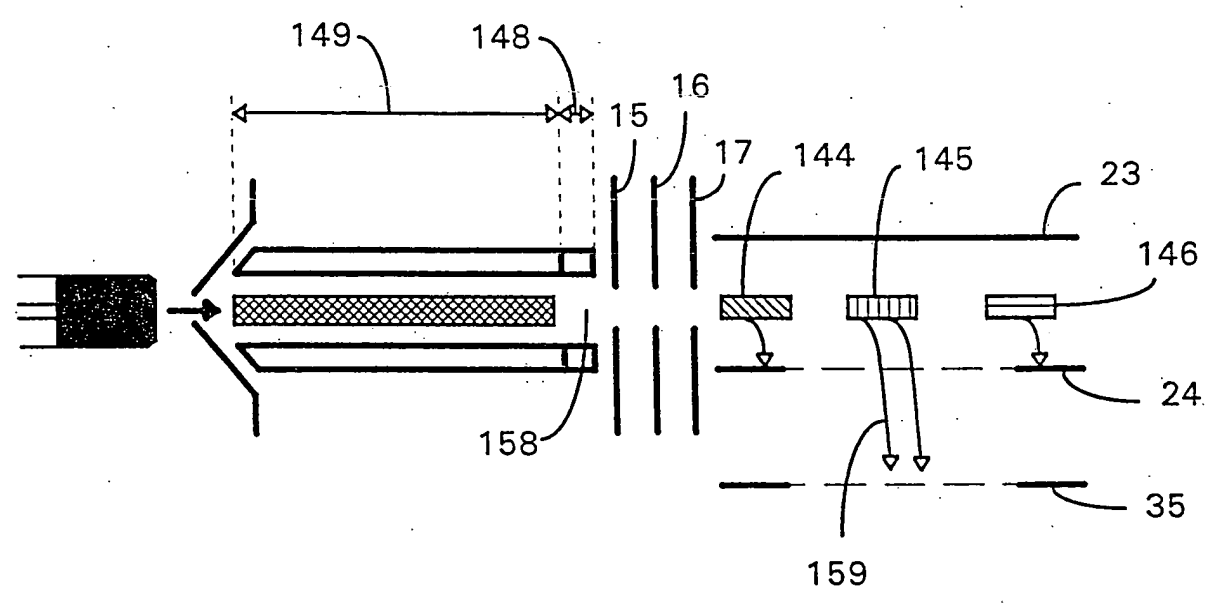


B

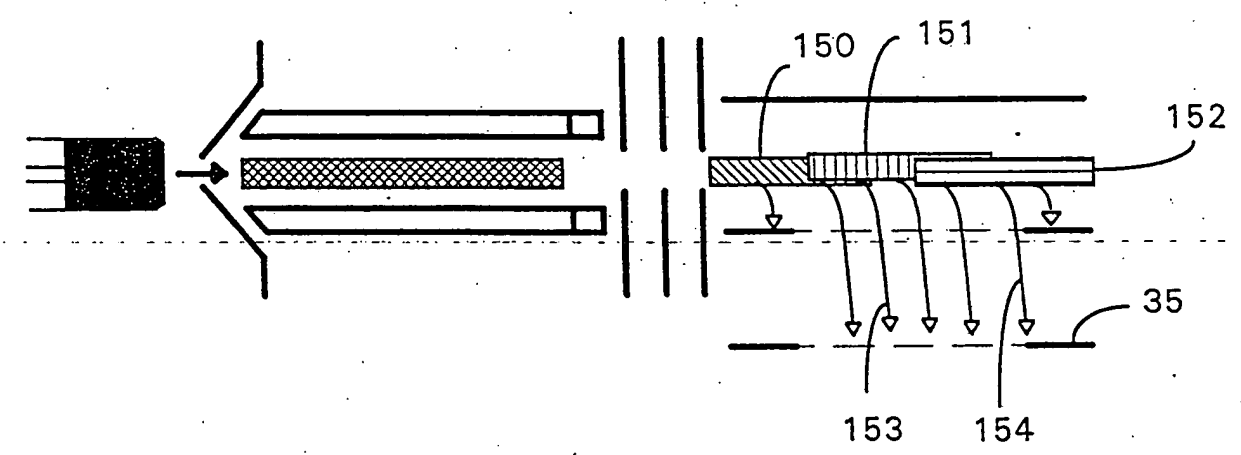
FIG. 10



A



B



C

FIG. 11

FOI090-89480860

[illegible]

FIG. 12